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Chen, Yunzhong

Publication date:
2015

Document Version
Peer reviewed version

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Citation (APA):

Chen, Y. (2015). *Charge Transfer Induced Modulation Doping at Oxide Interfaces*. Abstract from Rare earth-transitional metal oxides and compounds for environment-friendly energy science and technology, Beijing, China.

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Charge Transfer Induced Modulation Doping at Oxide Interfaces

Yunzhong Chen

Department of Energy Conversion and Storage, Technical University of Denmark, Risø DTU Campus, Denmark

Email:yunc@dtu.dk

Abstract:

The discovery of two-dimensional electron gases (2DEGs) at the interface between two insulating complex oxides, such as LaAlO_3 (LAO) or $\gamma\text{-Al}_2\text{O}_3$ (GAO) epitaxially grown on SrTiO_3 (STO) [1,2], provides an opportunity for developing all-oxide electronic devices[3,4]. However, large enhancement of the interfacial electron mobility remains a major and long-standing challenge for fundamental as well as applied research of complex oxides. Here, with in mind the intrinsic electronic structure of the STO 2DEG[5], we inserted a single unit cell insulating layer of polar $\text{La}_{1-x}\text{Sr}_x\text{MnO}_3$ ($x=0, 1/8, \text{ and } 1/3$) at the interface between disordered LaAlO_3 and crystalline SrTiO_3 created at room temperature. We find that the electron mobility of the interfacial 2DEG is enhanced by more than two orders of magnitude. Our in-situ and resonant x-ray spectroscopic in addition to transmission electron microscopy results indicate that the manganite layer undergoes unambiguous electronic reconstruction and leads to modulation doping of such atomically engineered complex oxide heterointerfaces. Moreover, the manganite spacer suppresses significantly the formation of oxygen vacancies on the STO side by preventing the interfacial redox reaction [6], which underlies the key to achieve the pure electronic reconstruction at the buffered interface [7]. At low temperatures, the modulation-doped 2DEG exhibits clear Shubnikov-de Haas oscillations and the initial manifestation of the quantum Hall effect, demonstrating an unprecedented high-mobility and low electron density oxide 2DEG system.

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Yunzhong Chen: He received his Ph.D. in Condensed Matter Physics in 2009 from Institute of Physics, Chinese Academy of Sciences, China. He is currently a senior researcher in Technical University of Denmark. His research focuses on the creation and understanding of the interface phenomena in atomically engineered complex oxide heterostructures, in particular the high-mobility 2DEG at the interface between insulating oxides.